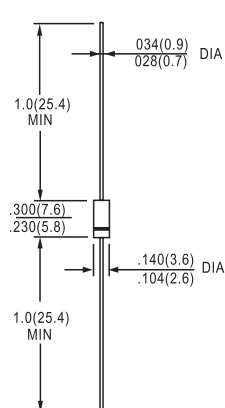


**TAYCHIPST****HIGH EFFICIENCY RECTIFIER****RU3YX(Z) THRU RU3C(Z)****100V-1000V 1.1A-2.0A****FEATURES**

- ◇ Low cost
- ◇ Diffused junction
- ◇ Low leakage
- ◇ Low forward voltage drop
- ◇ Easily cleaned with freon, alcohol, Isopropand and similar solvents
- ◇ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇ Case: JEDEC DO-15, molded plastic
- ◇ Terminals: Axial leads, solderable per MIL-STD-202, Method 208
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.024 ounces, 0.68 grams
- ◇ Mounting: Any



DO-15

Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

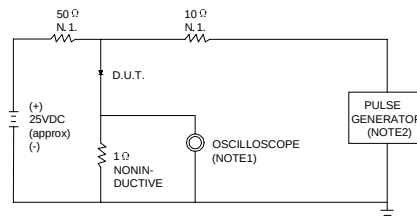
Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

		RU3YX	RU3	RU3A	RU3B	RU3C	UNITS
Maximum peak repetitive reverse voltage	V _{RRM}	100	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	70	280	420	560	700	V
Maximum DC blocking voltage	V _{DC}	100	400	600	800	1000	V
Maximum average forward rectified current 9.5mm lead length, @T _A =75°C	I _{F(AV)}	2.0	1.5		1.1	1.5	A
Peak forward surge current 10ms single half-sine-wave superimposed on rated load @T _J =125°C	I _{FSM}	50.0	20.0				A
Maximum instantaneous forward voltage @ I _F =I _{F(AV)}	V _F	0.95	1.5			2.5	V
Maximum reverse current @T _A =25°C at rated DC blocking voltage @T _A =100°C	I _R	10.0					μ A
		300.0	400.0				
Maximum reverse recovery time (Note1)	t _{rr}	50	100				ns
Typical junction capacitance (Note2)	C _J	50		30			pF
Typical thermal resistance (Note3)	R _{θJL}	12					°C/W
Operating junction temperature range	T _J	- 55 ----- + 150					°C
Storage temperature range	T _{STG}	- 55 ----- + 150					°C

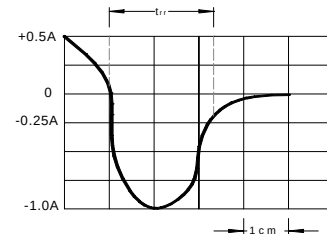
NOTE: 1. Measured with $I_F=0.5\text{A}$, $I_R=1\text{A}$, $I_{rr}=0.25\text{A}$

2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

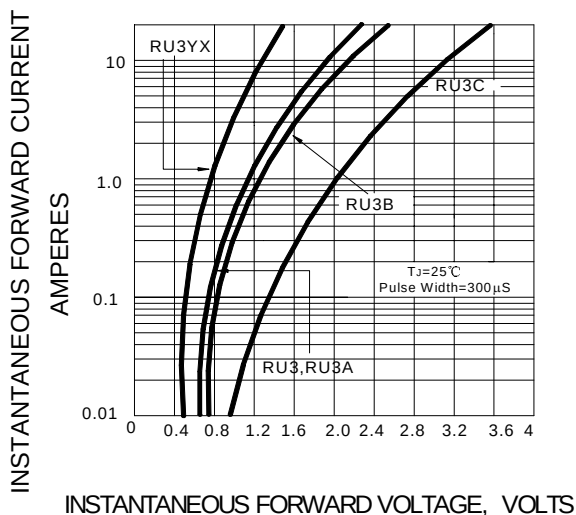
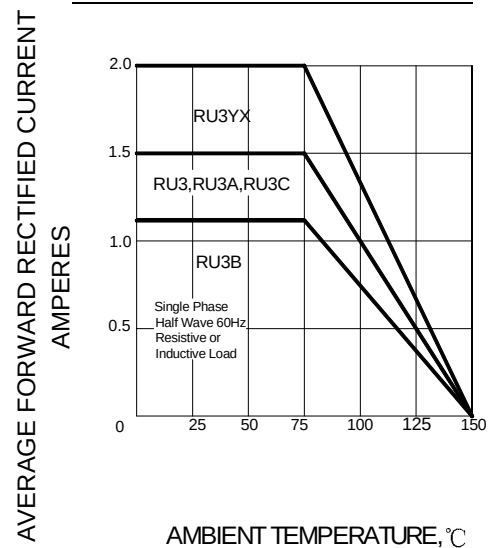
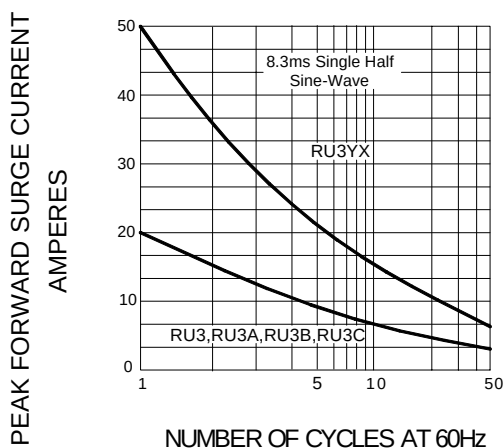
3. Thermal resistance junction to ambient.

**TAYCHIPST****HIGH EFFICIENCY RECTIFIER****RU3YX(Z) THRU RU3C(Z)****20V 5.0A****RATINGS AND CHARACTERISTIC CURVES RU3YX(Z) THRU RU3C(Z)****FIG.1 – TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC**

NOTES: 1. RISE TIME = 7ns MAX INPUT IMPEDANCE = 1MΩ, 22pF.
 2. RISE TIME = 10ns MAX. SOURCE IMPEDANCE = 50Ω.



SET TIME BASE FOR 10/20 ns/cm

FIG.2 – TYPICAL FORWARD CHARACTERISTIC**FIG.3 – FORWARD DERATING CURVE****FIG.4 – PEAK FORWARD SURGE CURRENT****FIG.5 – TYPICAL JUNCTION CAPACITANCE**